

**ELC1408- Level 1**

**Analog Electronics**

**Dr. Eman F. Sawires**

**Assistant Professor, Department of Electronics and Communications  
Engineering, Faculty of Engineering, Helwan University.**



# Lecture #1

# Course Introduction

# ➤ Course Details

<b>Course Code</b>	<b>ELC 1408</b>
<b>Course Name</b>	<b>Analog Electronics</b>
<b>Coordinating Unit</b>	<b>Electronics and Communications Engineering Department, Faculty of Engineering, Helwan University</b>
<b>Term</b>	<b>Semester 2 (Spring)</b>
<b>Level</b>	<b>Undergraduate -Level 1</b>

*E. Sawires*

# ➤ Course Staff

## ➤ Instructor

- Dr. Eman Farouk

## ➤ Teaching Assistant

- Eng. Eman Hasan
- Eng. Mohamed Hassan Elarabawy

*E. Sawires*

## الفصل الدراسي الثاني

الساعات المعتمدة	مجموع درجات المقرر	عدد ساعات الامتحان التحريرى	توزيع الدرجات	توزيع الدرجات			عدد الساعات الأسبوعية			اسم المقرر	كود المقرر
				تحريرى	على شفوى	أعمال سنة	مجموع	تطبيقات	محاضرة		
								تمرين	معلم		
3	100	3	70	-	30	4	-	2	2	الرياضيات الهندسية (4)	عام 1407
2	150	3	100	20	30	4	1	1	2	الإلكترونيات النظارية	إلك 1408
3	150	3	100	20	30	5	1	1	3	مقدمة الاتصالات	إلك 1409
3	150	3	100	30	20	4	2	-	2	برمجة الحاسب	حاس 1410
2	100	3	60	20	20	4	1	1	2	دوائر المنطق	إلك 1411
2	100	2	70	-	30	2	-	-	2	الكتاب التقنية	عام 1412
<b>15</b>		<b>عدد الساعات المعتمدة</b>				<b>23</b>	<b>5</b>	<b>5</b>	<b>13</b>	<b>اجمالى عدد الساعات الأسبوعية</b>	
	<b>1500</b>	<b>المجموع الكلى للدرجات</b>									

- تدريب صيفي بورش الإلكترونيات بالكلية لمدة ثلاثة أسابيع بعد امتحانات الفصل الدراسي الثاني للفرقه الأولى
- ترصد نتيجته (ناجح أو راسب فقط وبدون درجات) في الفصل الدراسي الأول للفرقه الثانية.

## ➤ Textbooks

- Sedra/Smith, “*Microelectronic circuits*”, Sixth edition.
- Floyd, “*Electronic Devices*”, 9th-edition.

*E. Sawires*

# ELC 1708: Course outlines

**The main contents of the course are:**

- Introduction
- Amplifiers
- Frequency response of amplifiers
  - Low-Frequency Response of the CS and CE Amplifiers
  - High-Frequency Response of the CS and CE Amplifiers
  - The High-Frequency Model of the MOSFET and the BJT

*E. Sawires*

# ELC 1708: Course outlines

**The main contents of the course are:**

- Differential Amplifiers
- Multistage amplifiers
  - RC coupling
  - Direct coupling
  - transformer coupling

# Introduction

- Semiconductors
- Diodes
- Transistors

*E. Sawires*

# Types of Transistors

- ❑ There are two major types of three-terminal semiconductor devices:
  - The bipolar junction transistor (BJT)
  - Field Effect Transistor (FET)
    - the metal-oxide semiconductor field-effect transistor (MOSFET)

*E. Sawires*

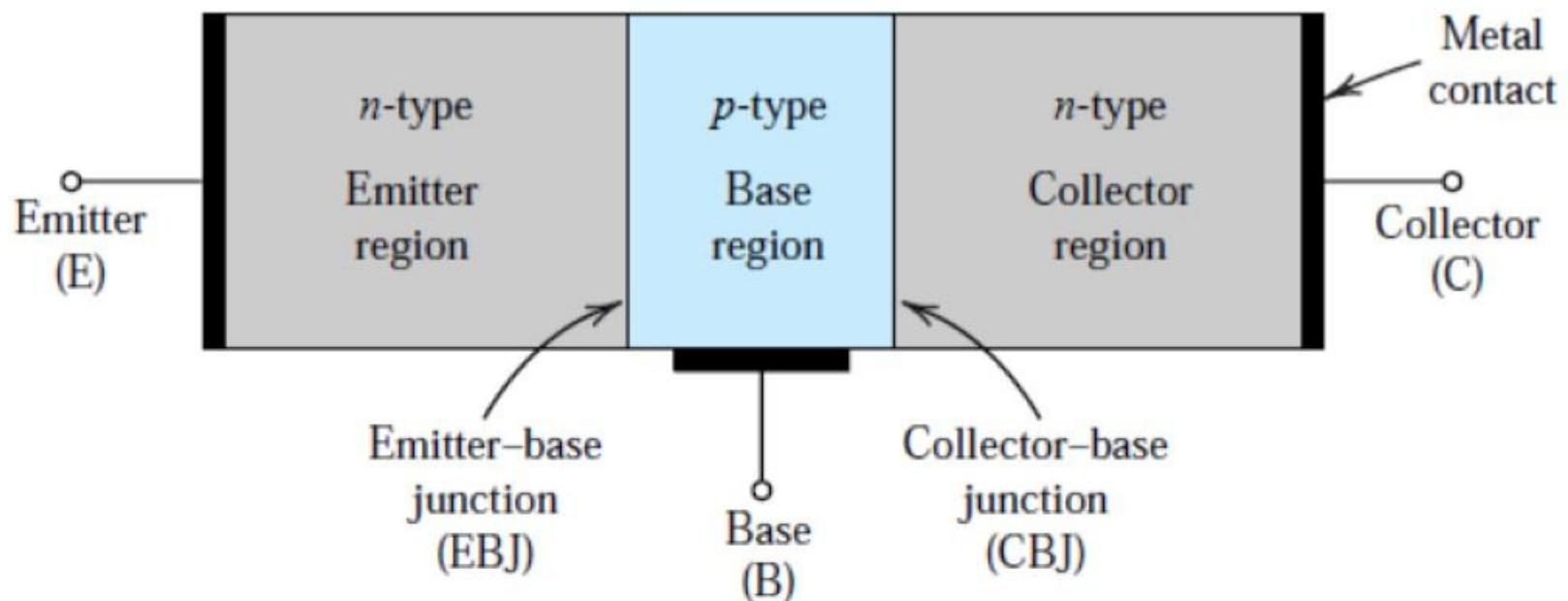
## Uses of Transistors

- Electrically controlled switch (digital circuits/computers)
- Amplifier
- Resistor with value electrically controlled

*E. Sawires*

# The bipolar junction transistor (BJT)

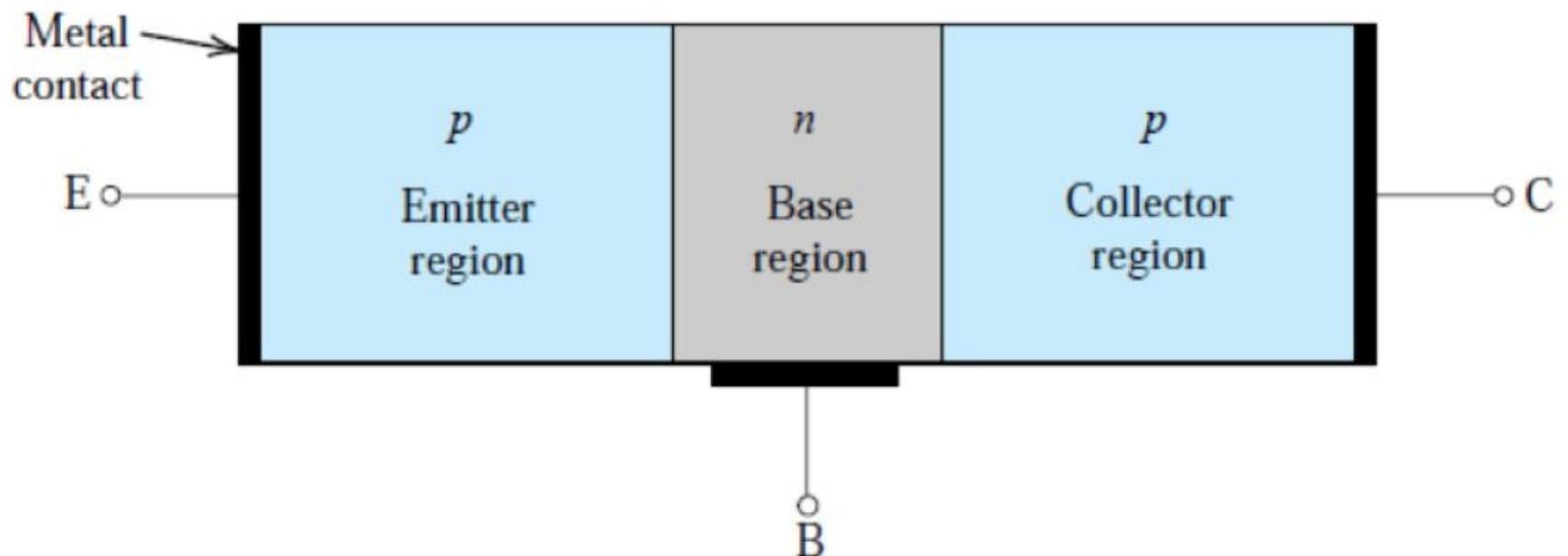
# Structure of Bipolar Junction Transistor



A simplified structure of the *npn* transistor.

*E. Sawires*

# Structure of Bipolar Junction Transistor



A simplified structure of the *pnp* transistor.

*E. Sawires*

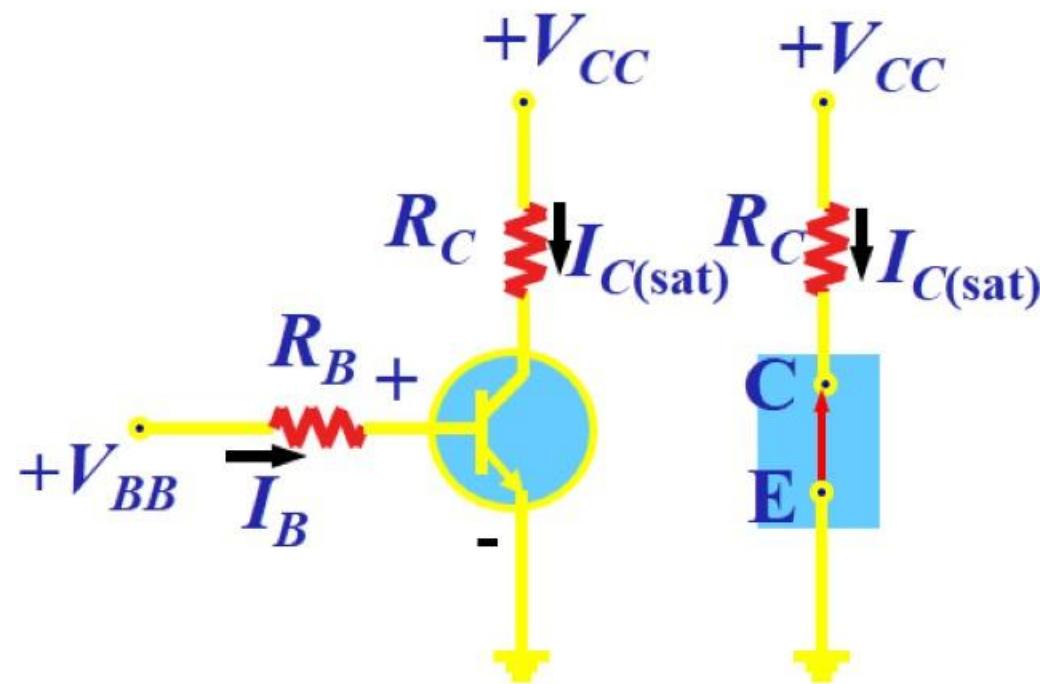
# Regions of Operation

Emitter-Base junction	Collector-Base junction	Mode of operation	Applications
Reverse	Reverse	Cutoff mode	Electronic Switch
Forward	Forward	Saturation mode	
Forward	Reverse	Active mode	Amplifier

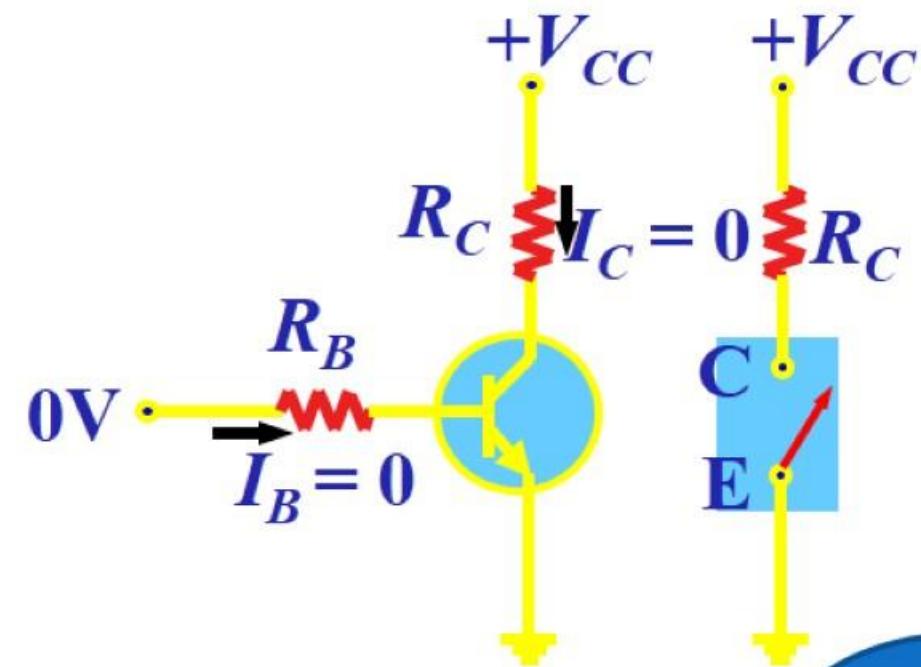
# Transistor Applications

# The Bipolar Transistor as a Switch

When used as an electronic switch, a transistor is normally operated alternately in cutoff and saturation.



Saturation –Closed switch

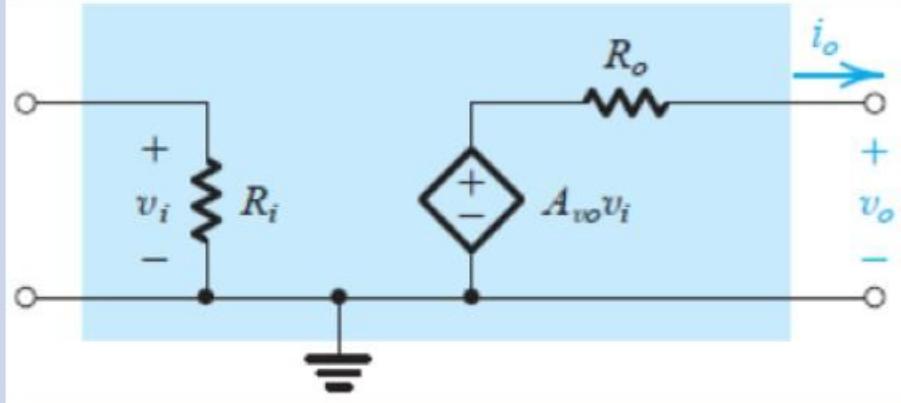
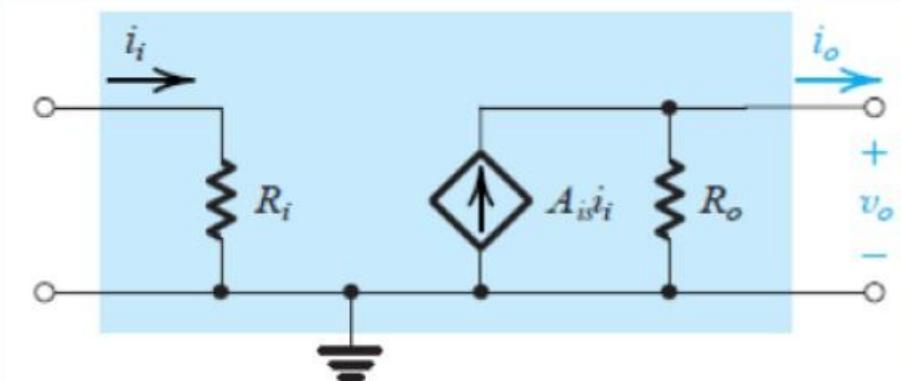


Cutoff – open switch

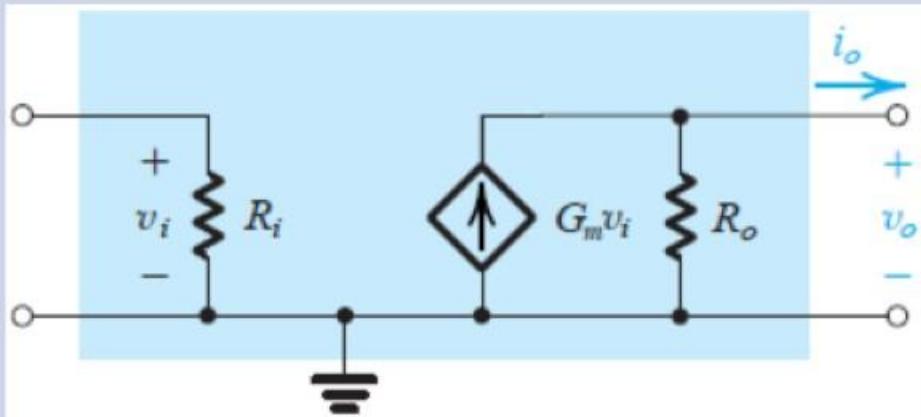
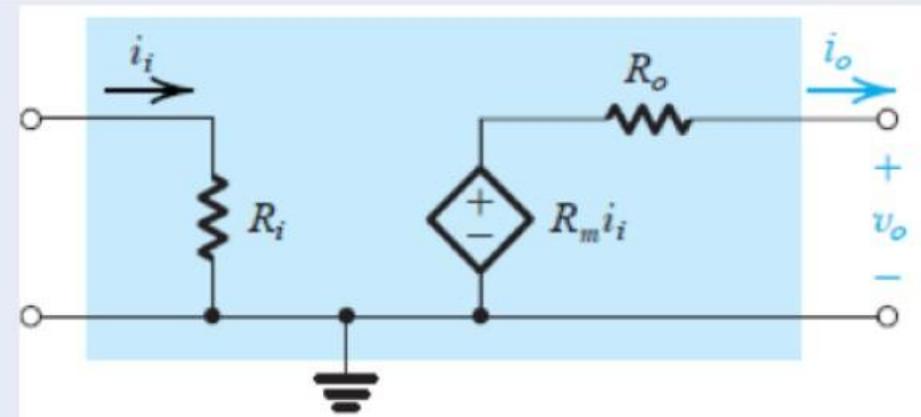
*E. Sawires*

# The BJT as an Amplifier

## The Four Amplifier Types:

Type	Circuit Model	Gain Parameter	Ideal Characteristics
Voltage amplifier		<b>Open circuit voltage gain</b> $=A_{vo} = \frac{v_o}{v_i} \Big _{i_o=0}$ (V/V)	$R_i = \infty$ , $R_o = 0$
Current amplifier		<b>Short circuit current gain</b> $=A_{is} = \frac{i_o}{i_i} \Big _{v_o=0}$ (A/A)	$R_i = 0$ , $R_o = \infty$

## The Four Amplifier Types:

Type	Circuit Model	Gain Parameter	Ideal Characteristics
Transconductance amplifier		<b>Short circuit Transconductance</b> $= G_m = \frac{i_o}{v_i} \Big _{v_o=0}$ (A/V)	$R_i = \infty$ , $R_o = \infty$
Transresistance amplifier		<b>Open circuit Transresistance</b> $= R_m = \frac{v_o}{i_i} \Big _{i_o=0}$ (V/A)	$R_i = 0$ , $R_o = 0$

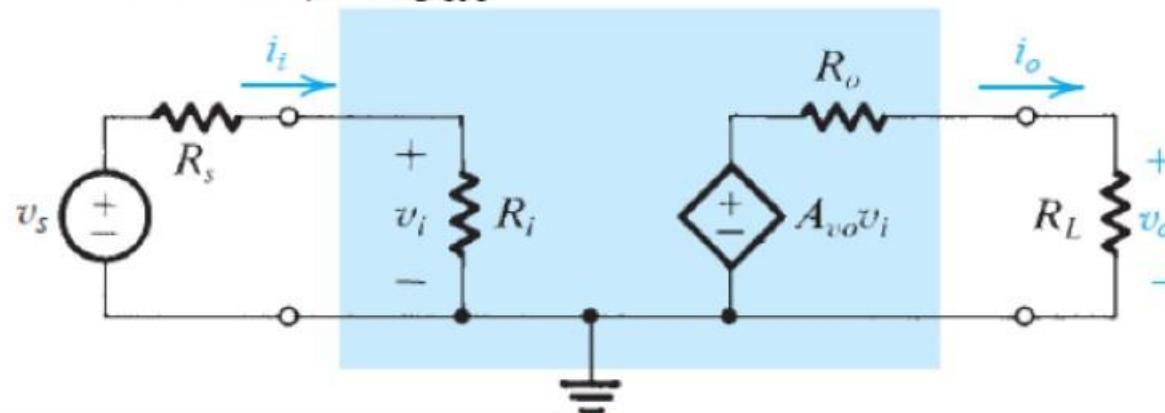
# Objective

- Implementing a voltage amplifier Circuit on the transistor level
- **What are the Specifications for an Ideal Voltage Amp.?**

- Infinite Input Resistance:  $R_{in}$
- Infinite **open circuit voltage gain.**:  $A_{vo}$
- Finite Output Resistance (Short Circuit):  $R_{out}$

$$A_{vo} \equiv \left. \frac{v_o}{v_i} \right|_{R_L=\infty}$$

$$A_v = \frac{v_o}{v_i} = A_{vo} \frac{R_L}{R_L + R_o}$$

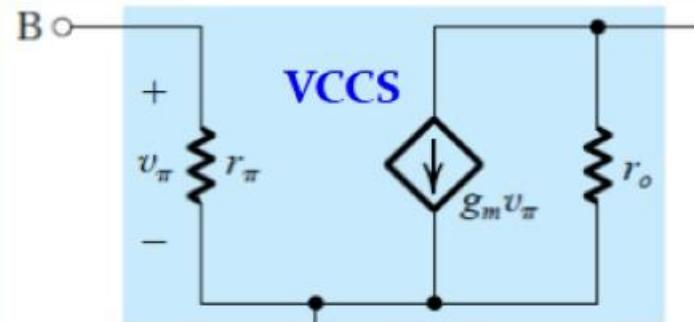


The overall voltage gain  $G_v = \frac{v_o}{v_s} = A_{vo} \frac{R_L}{R_L + R_o} \frac{R_i}{R_i + R_s}$

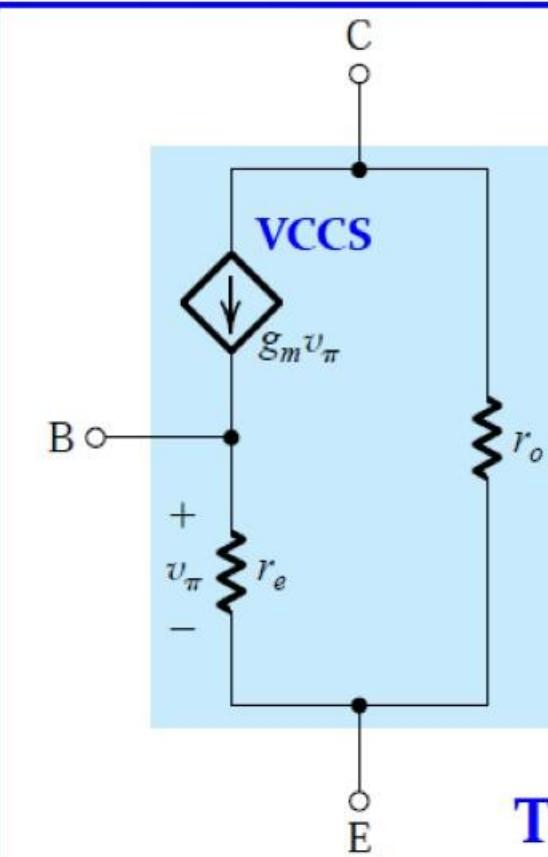
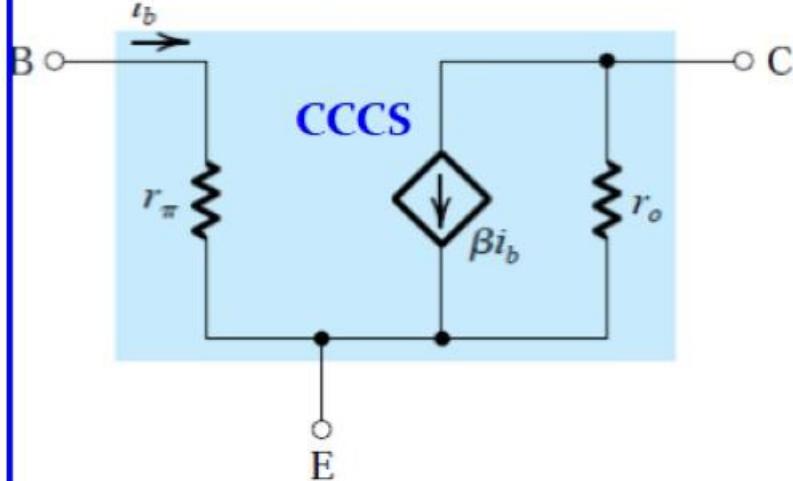
E. Sawires

# BJT Amplifiers Configurations

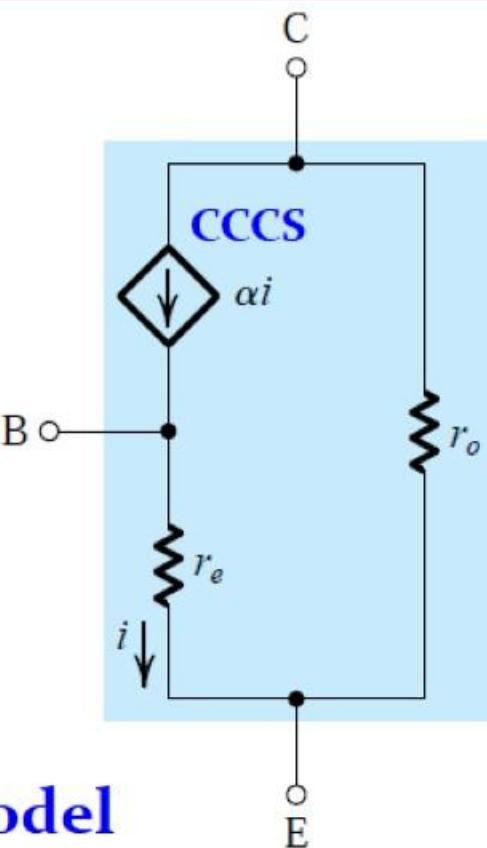
# Summary of the Small Signal Models of BJT



**Hybrid  $\pi$  model**



**T model**



**Model Parameters in Terms of DC Bias Currents**

$$g_m = \frac{I_c}{V_T}$$

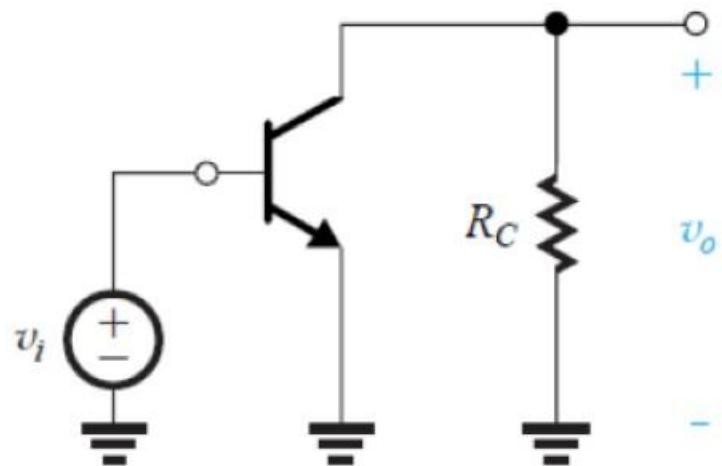
$$r_\pi = \frac{V_T}{I_B} = \beta \frac{V_T}{I_C}$$

$$r_e = \frac{V_T}{I_E} = \alpha \frac{V_T}{I_C} = \frac{\alpha}{g_m}$$

$$r_o = \frac{|V_A|}{I_C}$$

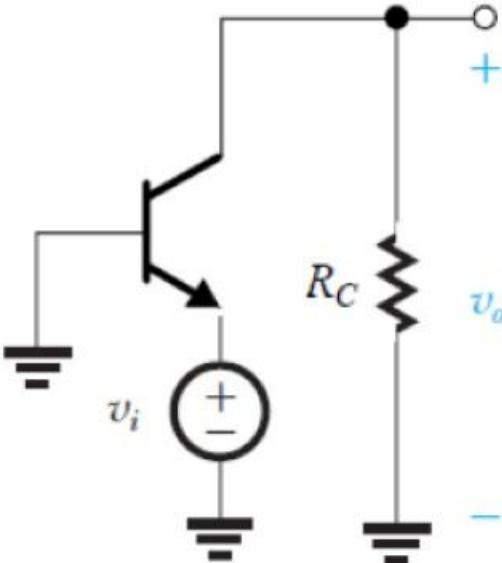
# Basic Configurations of BJT Amplifiers

- There are three basic configurations for connecting the BJT as an amplifier. Each of these configurations is obtained by connecting one of the three BJT terminals to ground, thus creating a two-port network with the grounded terminal being *common* to the input and output ports.

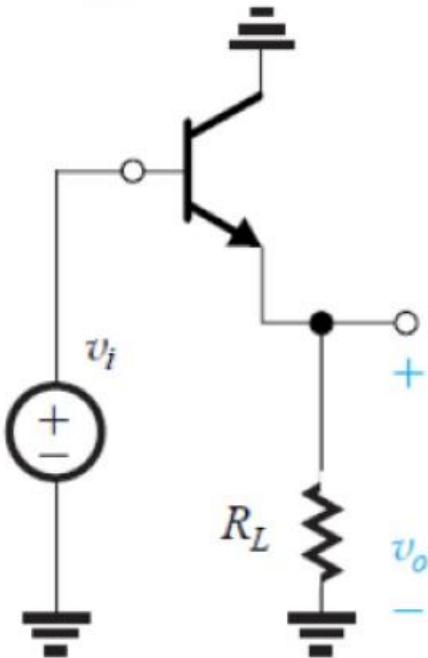


**Common emitter**

**It is the mostly used configuration**

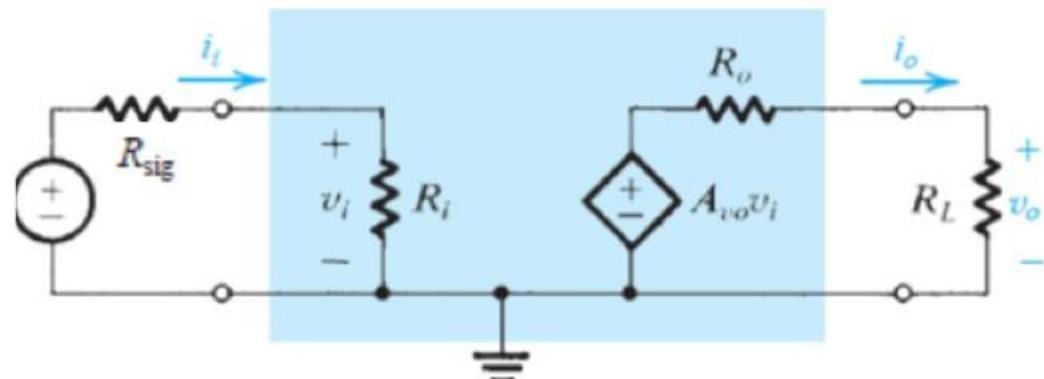
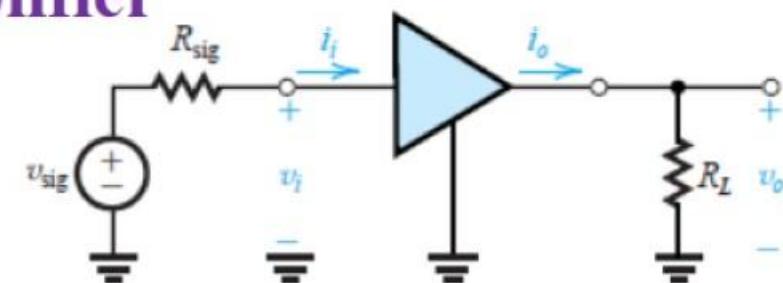
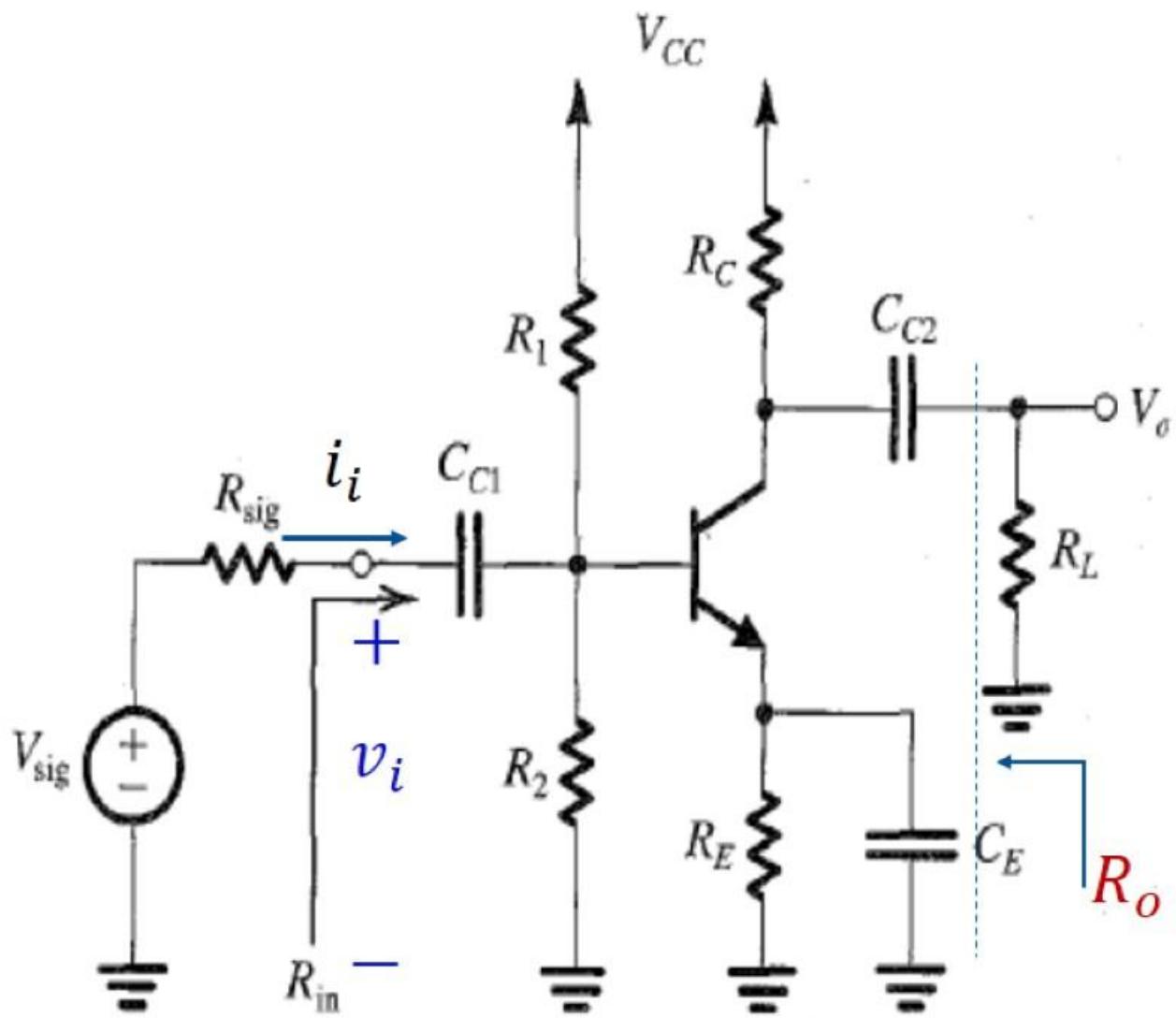


**Common Base**



**Common collector**

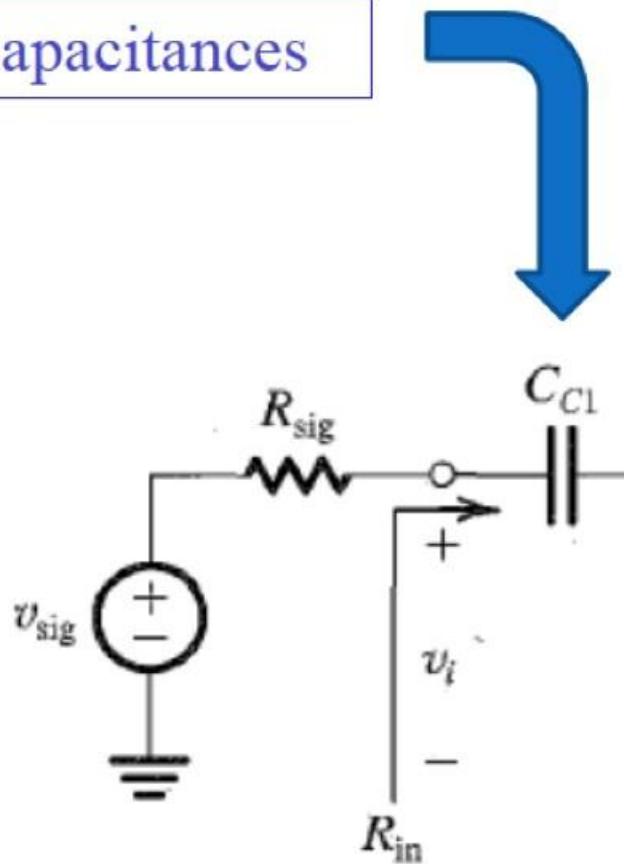
# The Common Emitter Amplifier



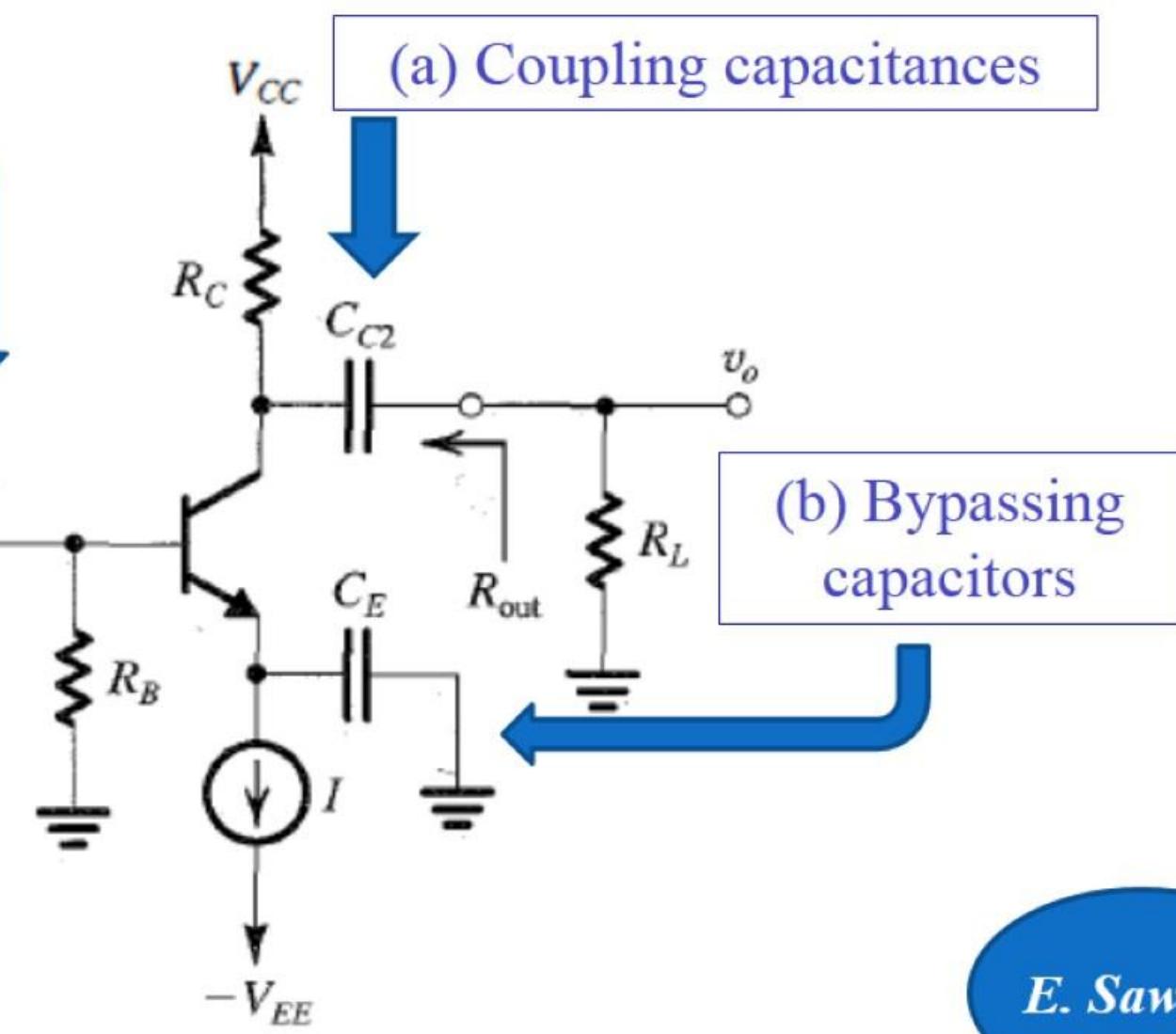
# The Common Emitter Amplifier

## Example:

(a) Coupling capacitances



(a) Coupling capacitances



(b) Bypassing capacitors

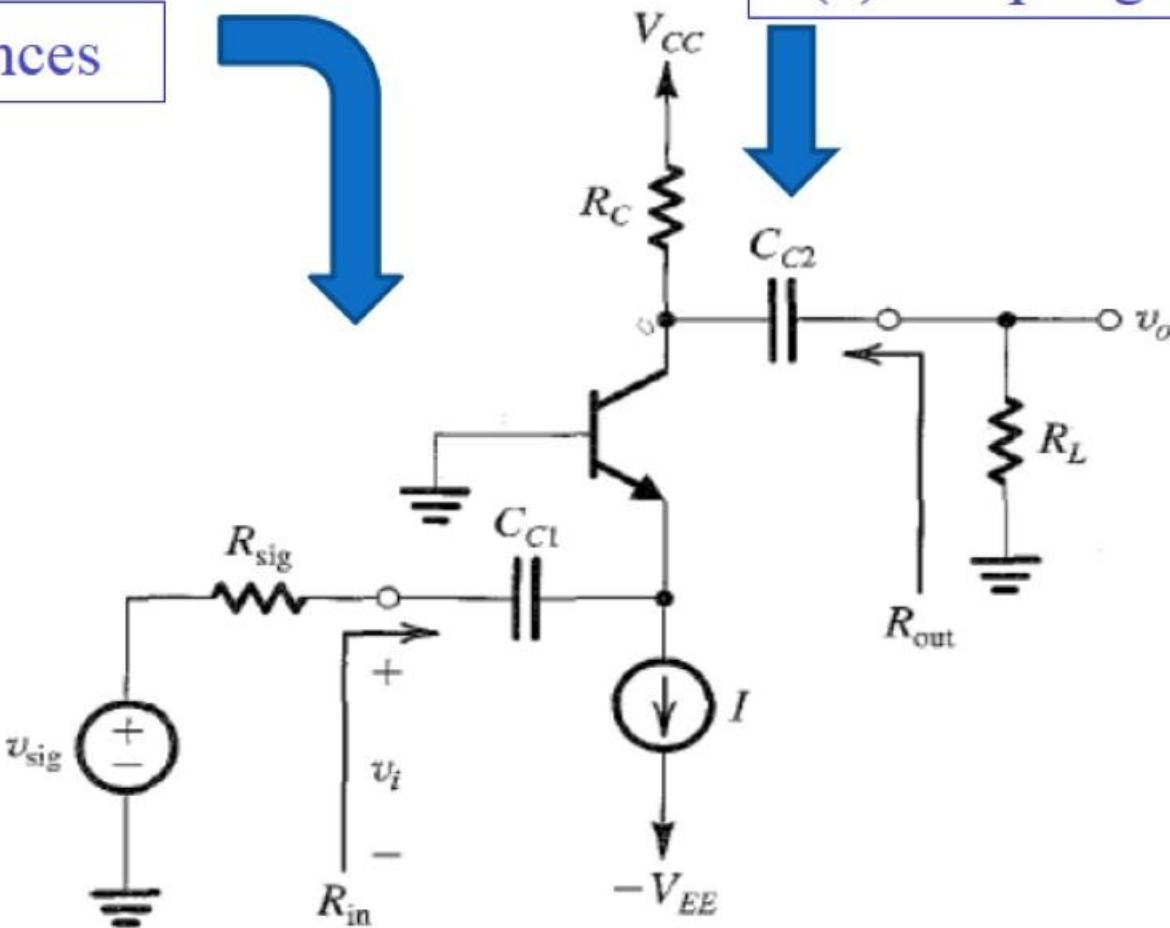
E. Sawires

# The Common Base Amplifier

(a) Coupling capacitances



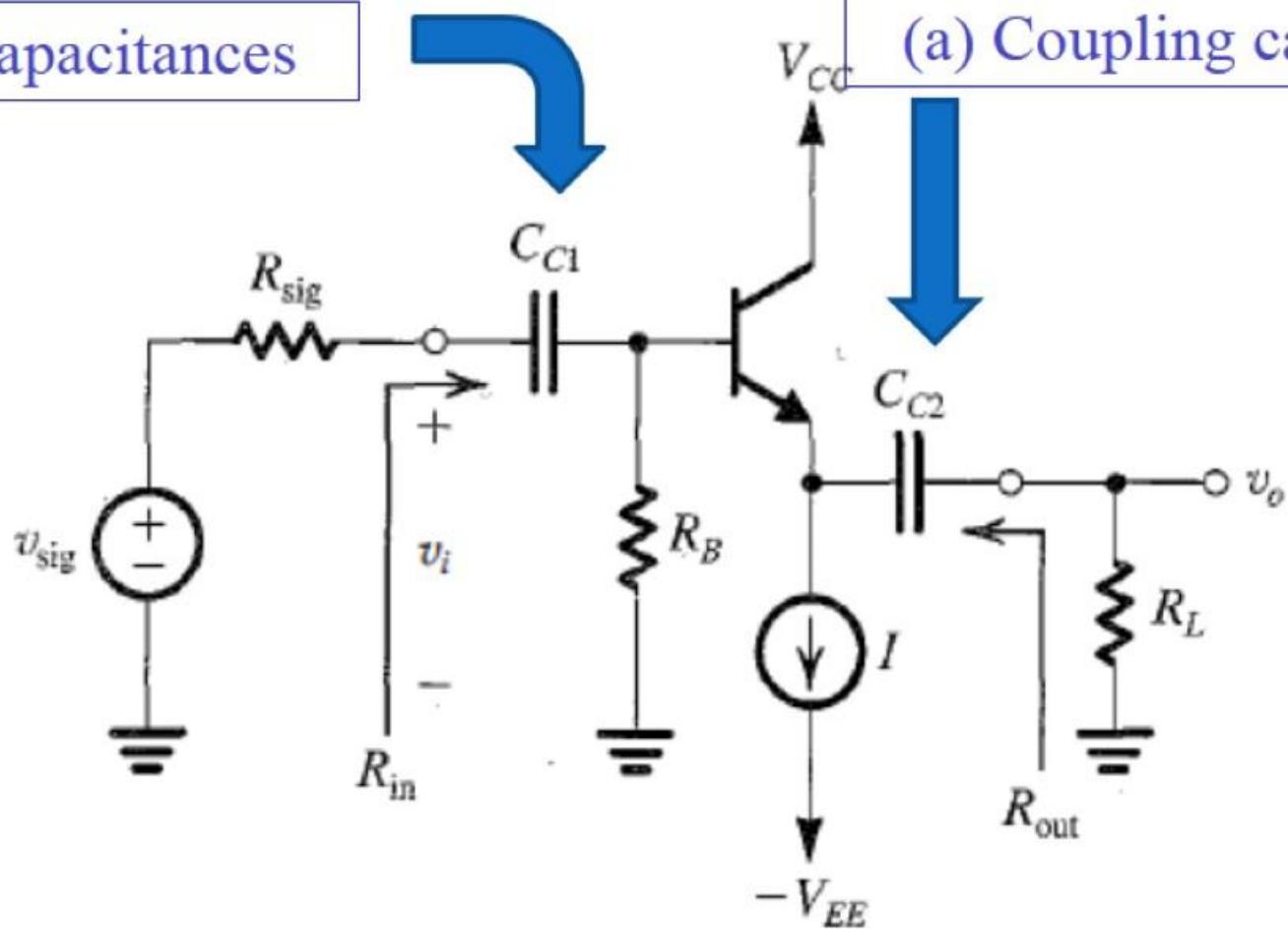
(a) Coupling capacitances



# Common Collector Amplifier or Emitter Follower

# The Common Collector, CC, or Emitter follower Amplifier

(a) Coupling capacitances



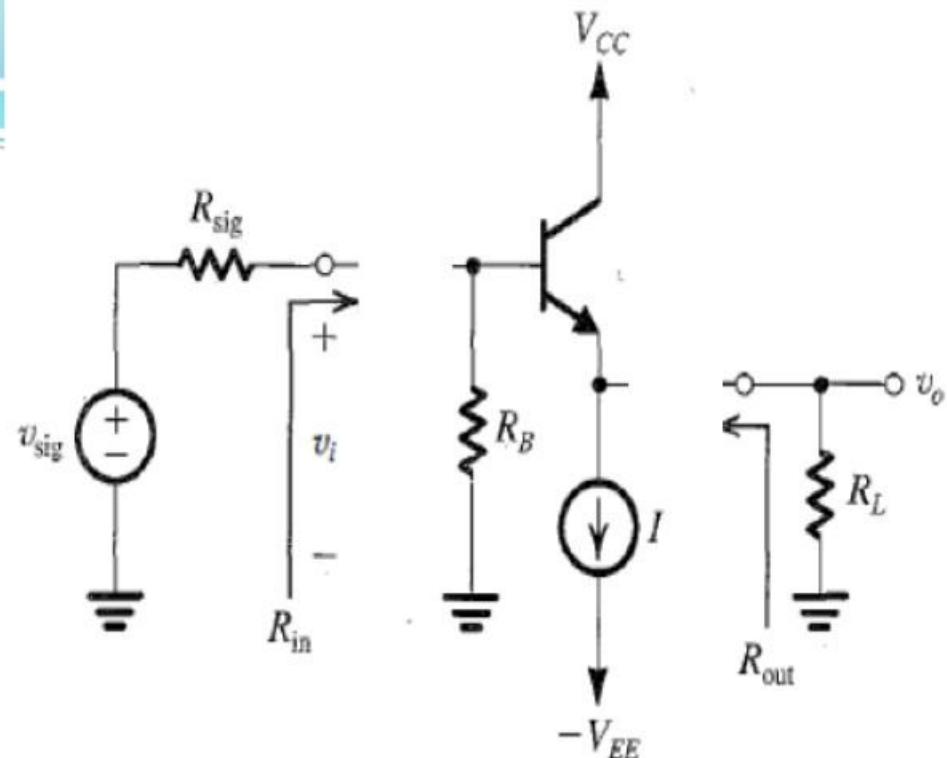
(a) Coupling capacitances

## DC analysis

- To find the DC operating point ( $I_B$ ,  $I_C$ ,  $I_E$ ,..., and mode of operation).
- To Calculate  $g_m$ ,  $r_\pi$ ,  $r_e$ ,  $r_0$  using:
  - $f=0$

$$Z_C = \frac{1}{sc} = \frac{1}{j2\pi f C} \cong \infty$$

all capacitors are open circuit



## DC analysis

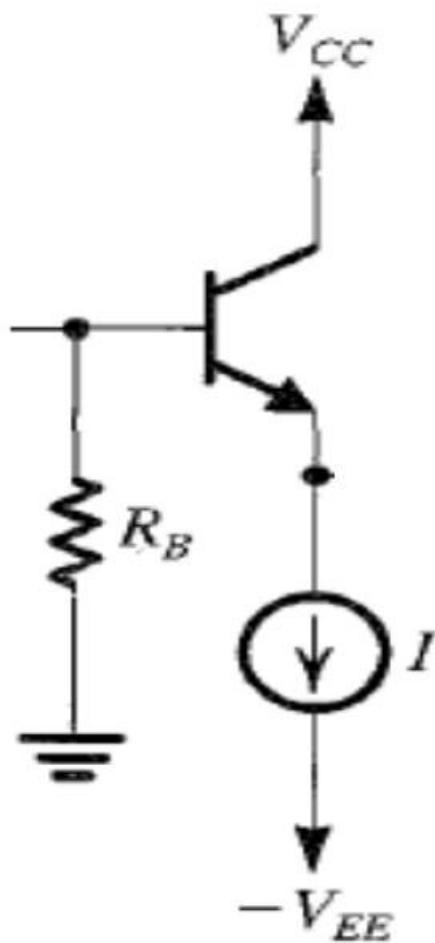
$$I_E = I$$

$$r_e = \frac{V_T}{I_E} = \alpha \frac{V_T}{I_C} = \frac{\alpha}{g_m}$$

$$g_m = I_C/V_T$$

$$r_\pi = V_T/I_B = \beta/g_m$$

$$r_o = \frac{|V_A|}{I_C} = \frac{|V_A|}{\beta I_B}$$



## AC analysis

- To find the  $R_i$ ,  $R_o$ ,  $A_{Vo}$ ,  $A_V$ ,  $G_V$ .

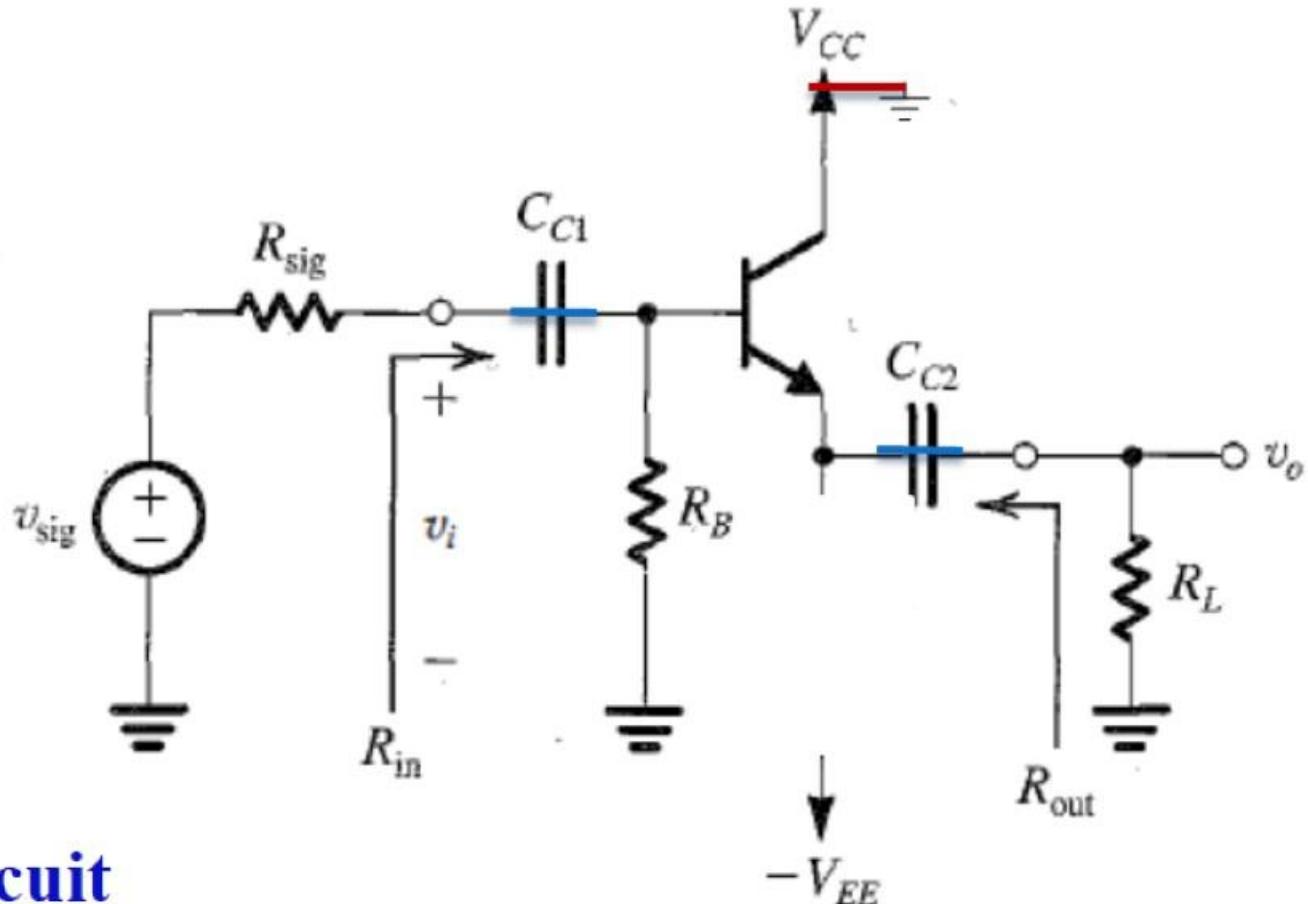
$$Z_{Cext} = \frac{1}{SC} = \frac{1}{j2\pi f C} \approx 0$$

all capacitors are short circuit

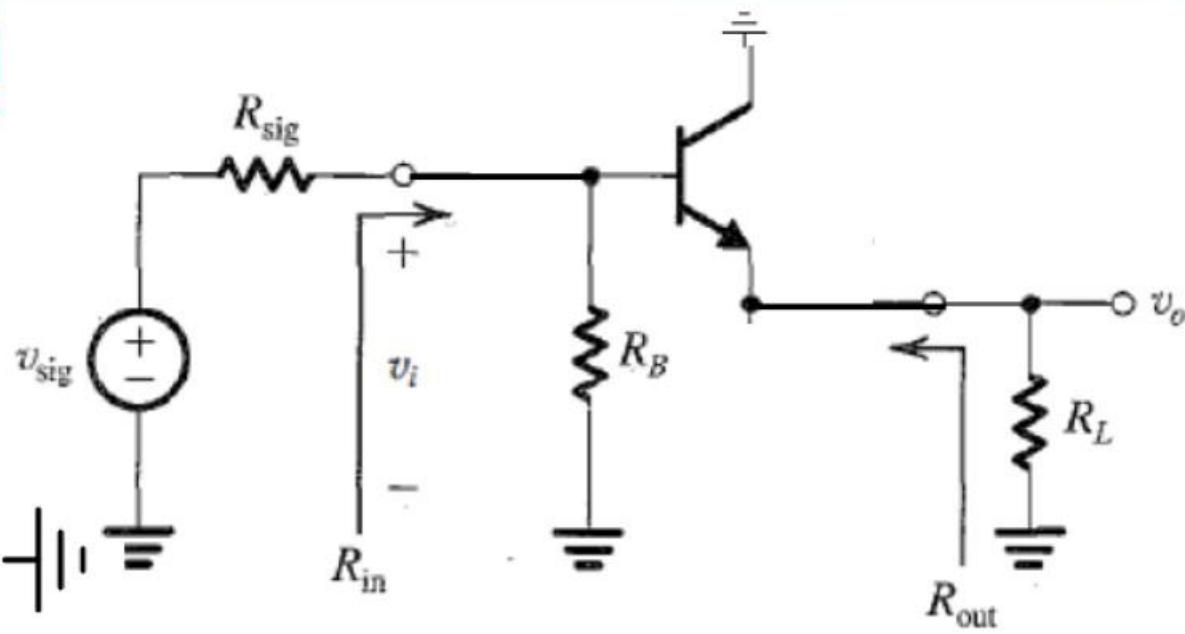
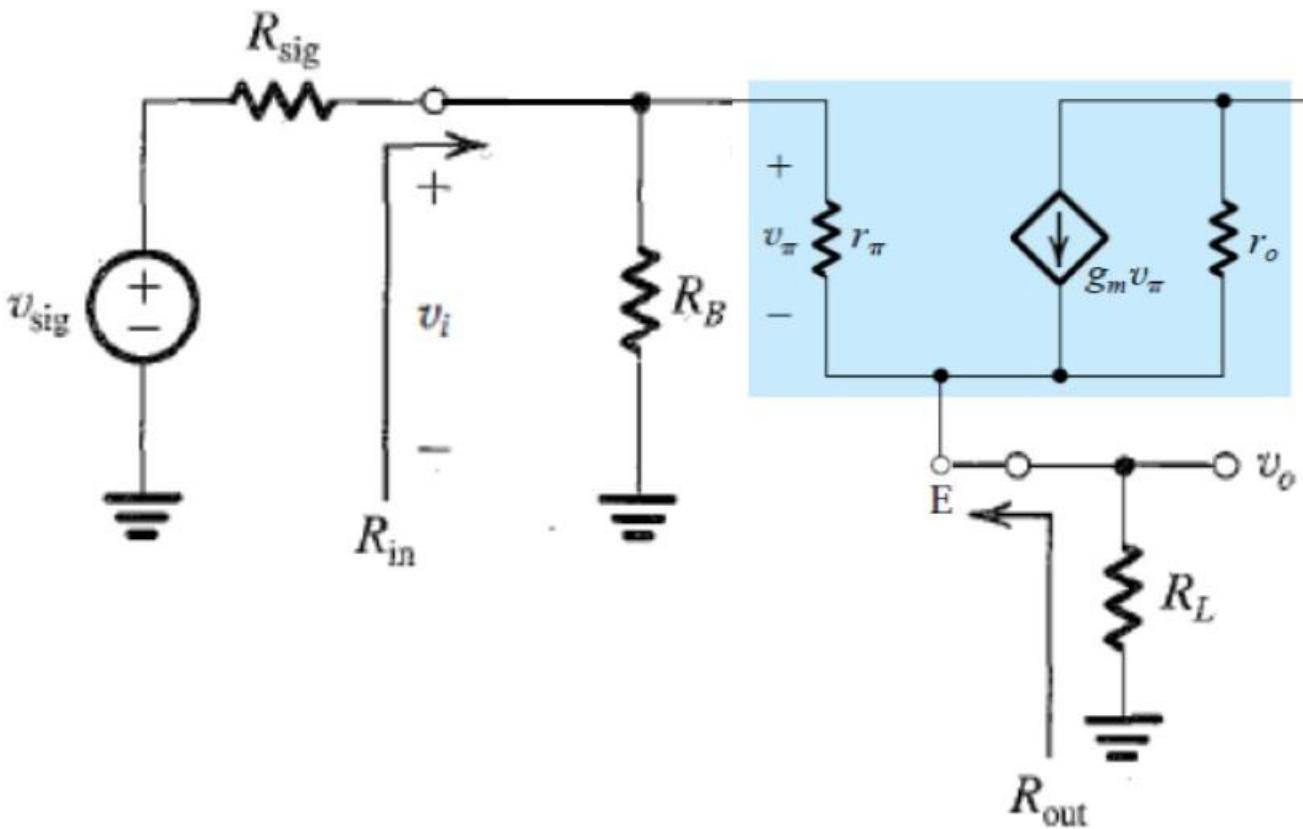
all DC sources → neglected

Voltage DC sources >> Short circuit

Current DC sources >> open circuit



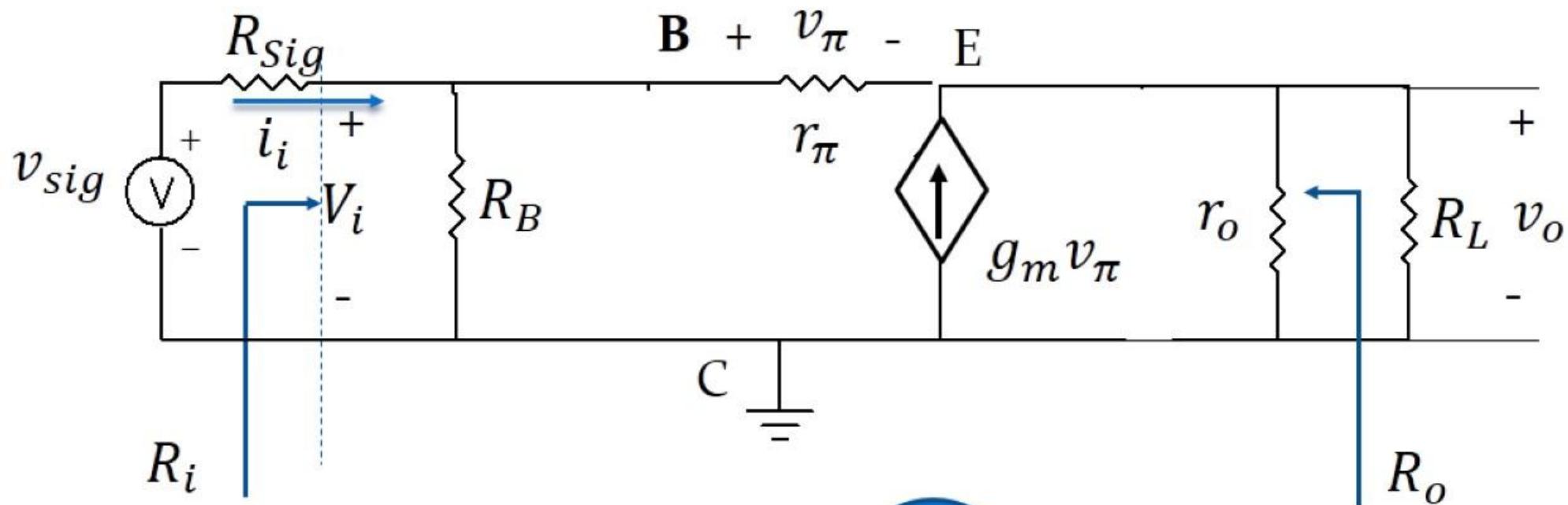
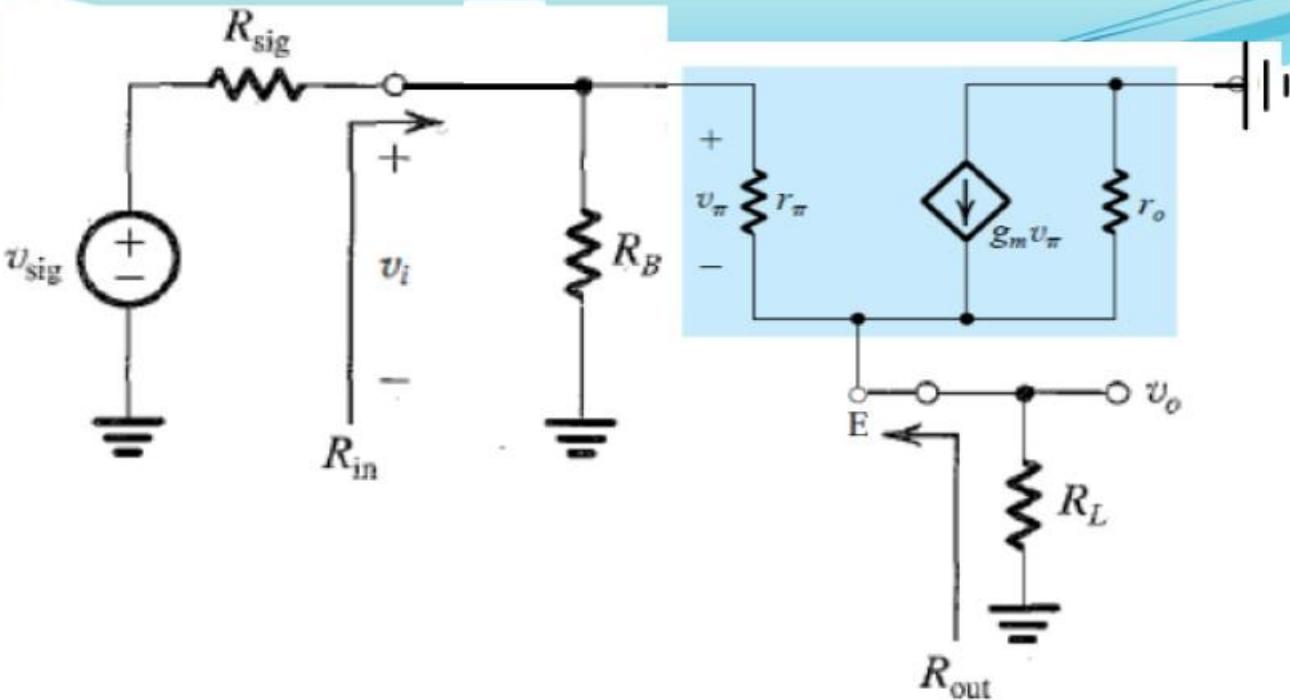
# AC analysis



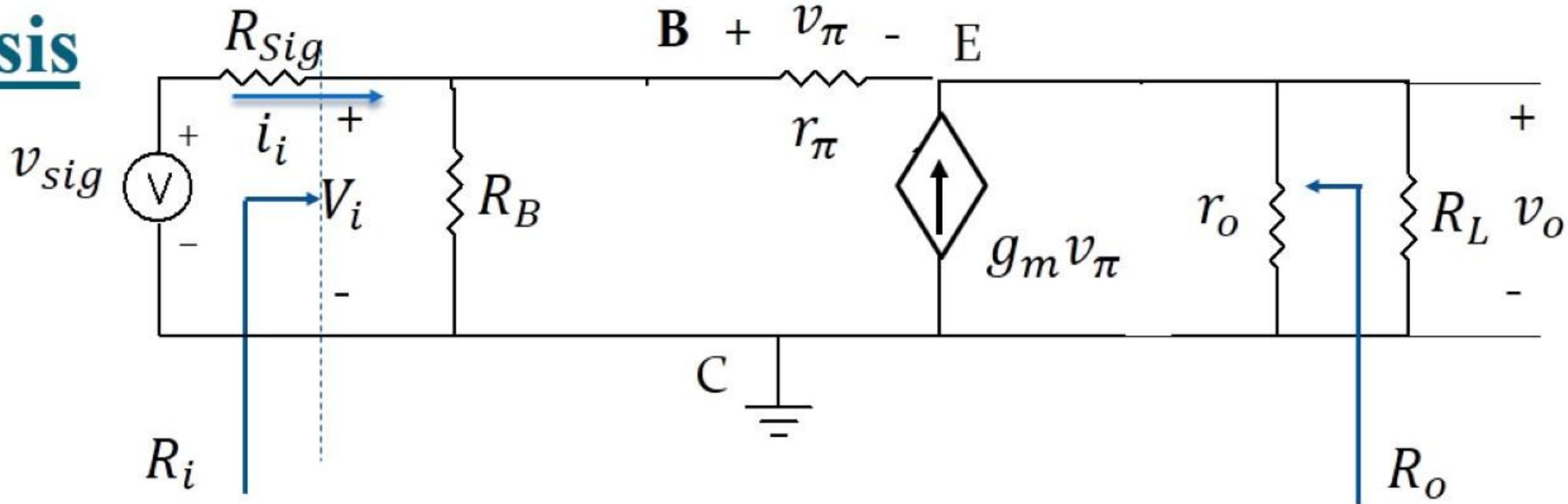
The AC (small-signal) equivalent circuit

E. Sawires

## AC analysis



## AC analysis



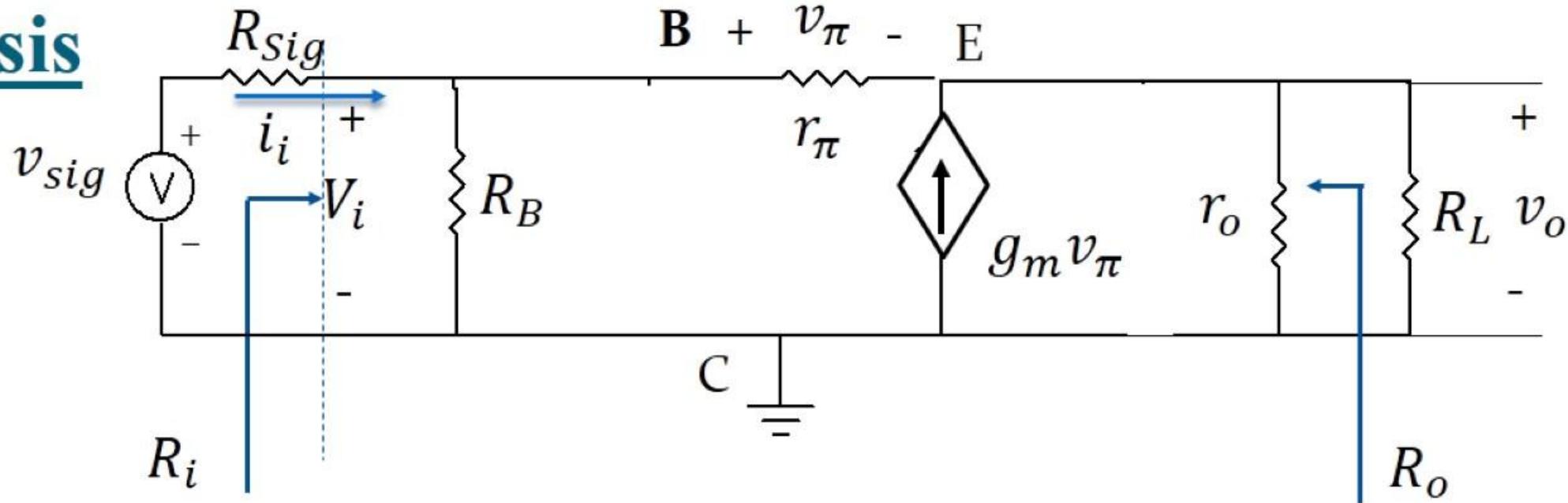
$$v_i = v_o + v_\pi$$

$$v_o = (r_o \parallel R_L) \left( g_m v_\pi + \frac{v_\pi}{r_\pi} \right) = \frac{v_\pi}{r_\pi} (r_o \parallel R_L) (g_m r_\pi + 1) = \frac{v_\pi}{r_\pi} (r_o \parallel R_L) (\beta + 1)$$

$$v_i = v_o + \frac{v_o r_\pi}{(r_o \parallel R_L)(\beta + 1)}$$

E. Sawires

## AC analysis



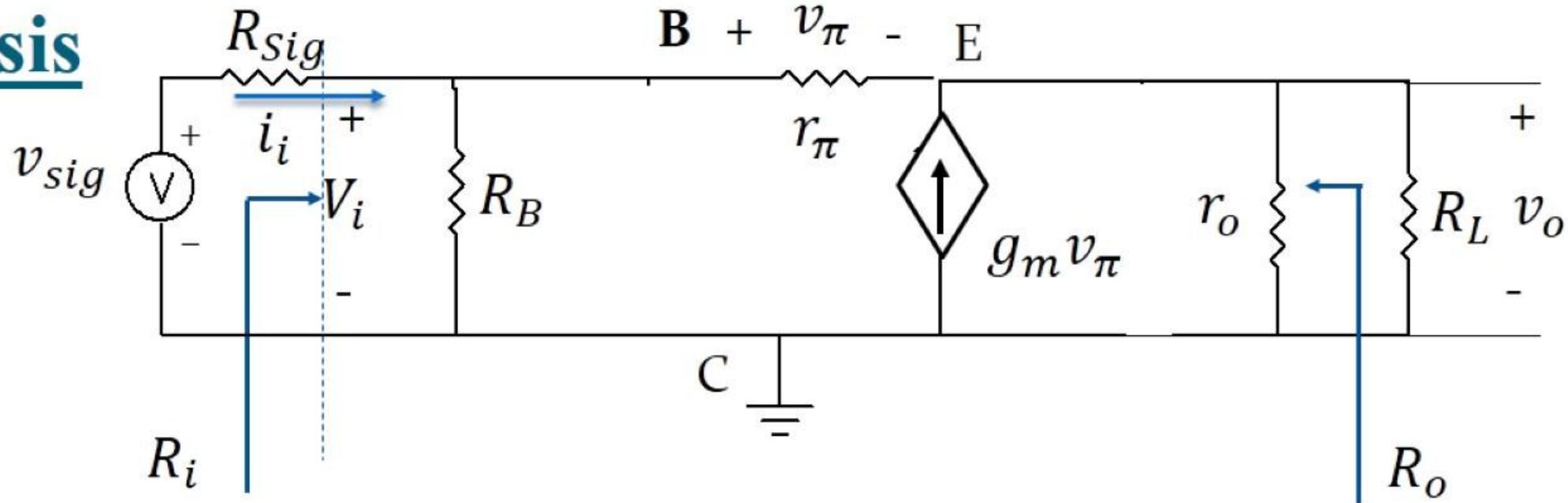
$$A_v = \frac{v_o}{v_i} = \frac{(r_o || R_L)(\beta + 1)}{(r_o || R_L)(\beta + 1) + r_\pi} = \frac{(r_o || R_L)}{(r_o || R_L) + r_e} < 1$$

$$A_{vo} = A_v \underset{\text{At } R_L = \infty}{\cong} 1$$

At  $R_L = \infty$

➤  $A_{vo} = 1$  means that the signal voltage at the emitter follows that at the base, this why it is called emitter follower.

## AC analysis

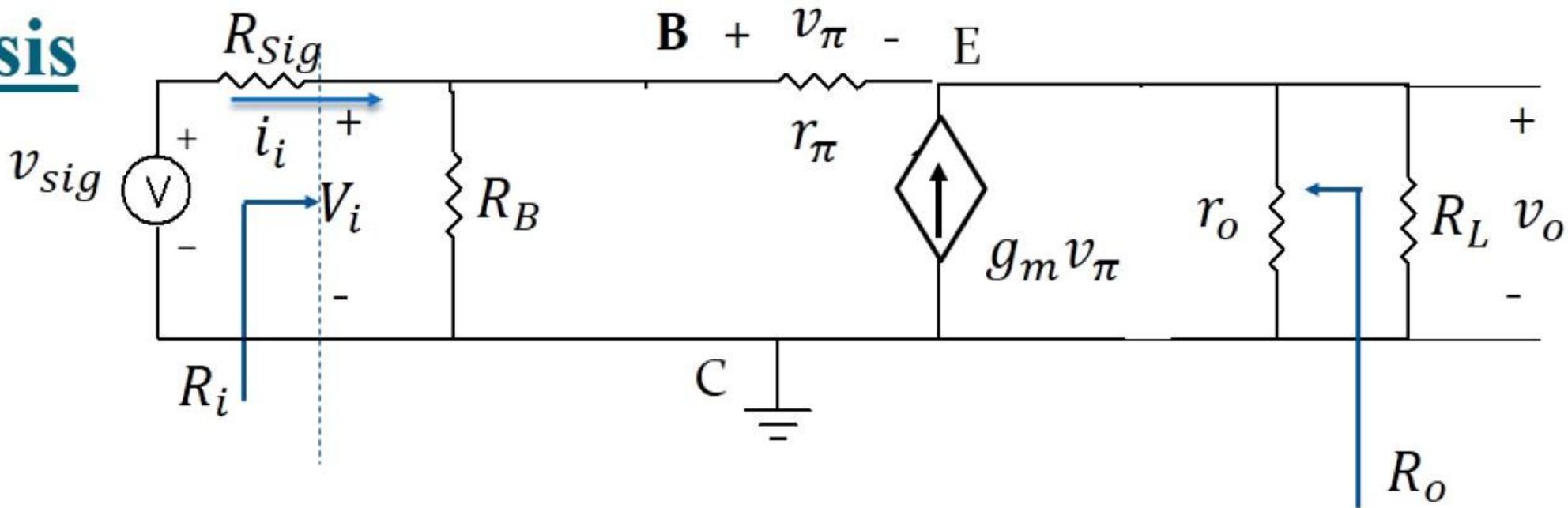


overall gain:  $G_v = \frac{v_o}{v_{sig}} = \frac{v_i}{v_{sig}} \times A_v = \frac{R_{in}}{R_{in} + R_{sig}} \times A_v$

E. Sawires

## AC analysis

$$i_i = \frac{v_i}{R_B} + \frac{v_\pi}{r_\pi}$$

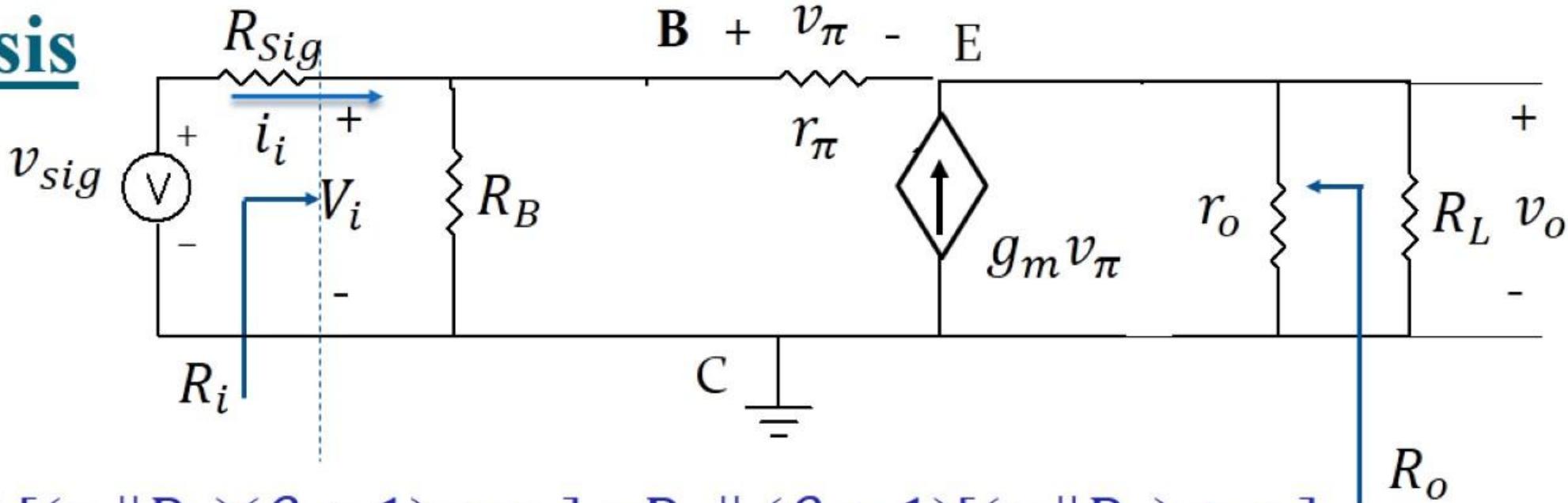


$$v_i = v_o + v_\pi = \frac{v_\pi}{r_\pi} (r_o \| R_L)(\beta + 1) + v_\pi = \frac{v_\pi}{r_\pi} [(r_o \| R_L)(\beta + 1) + r_\pi]$$

$$i_i = \frac{v_i}{R_B} + \frac{v_i}{[(r_o \| R_L)(\beta + 1) + r_\pi]}$$

E. Sawires

## AC analysis

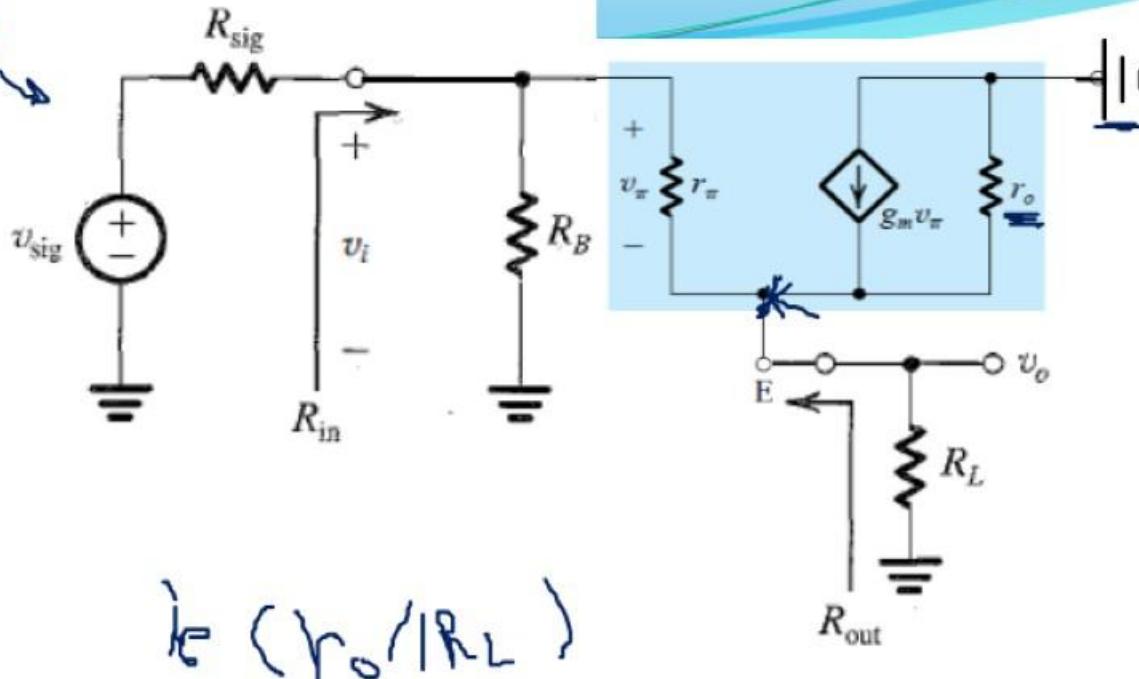
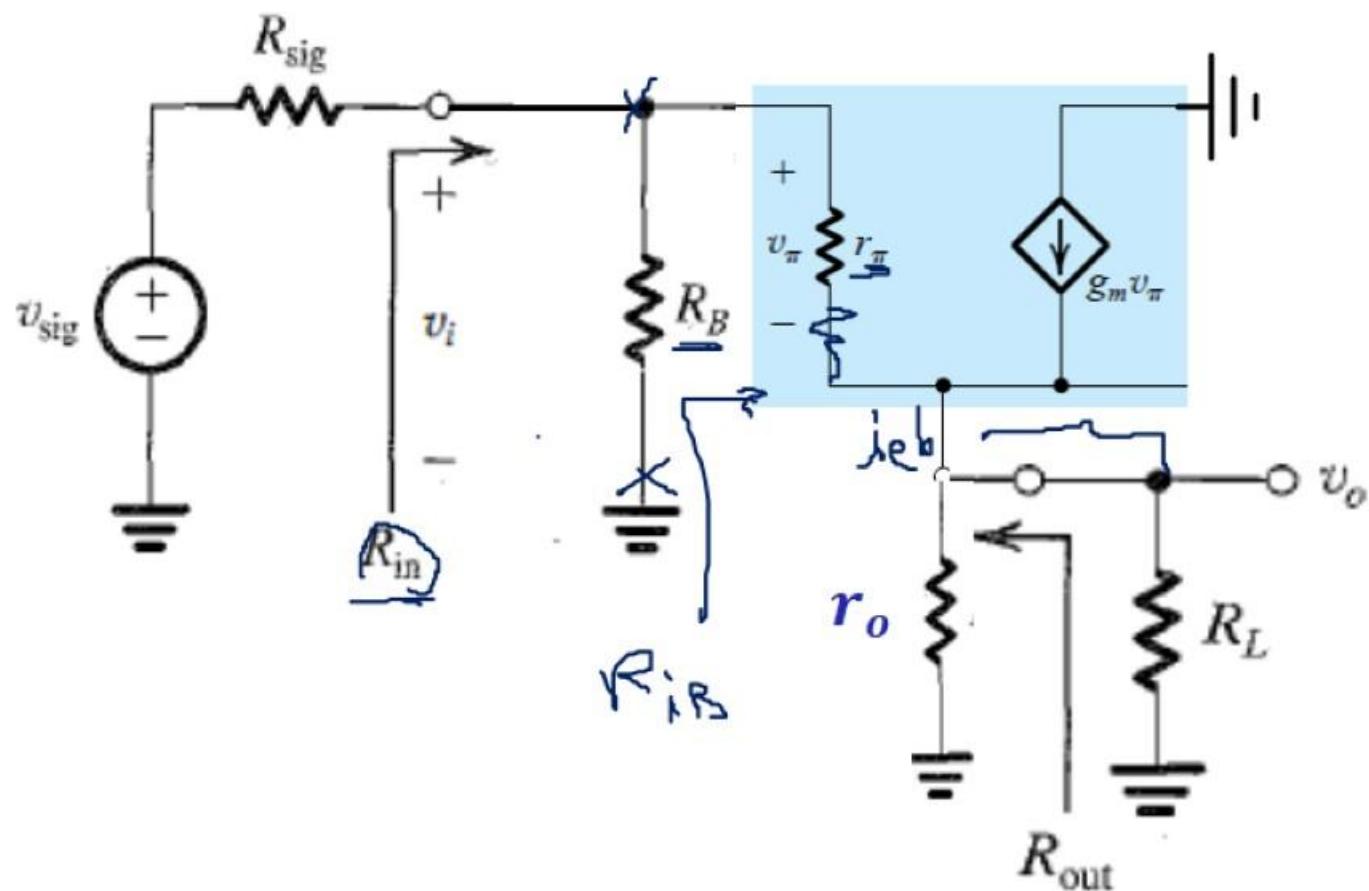


$$R_i = \frac{v_i}{i_i} = R_B \parallel [(r_o \parallel R_L)(\beta + 1) + r_\pi] = R_B \parallel (\beta + 1)[(r_o \parallel R_L) + r_e]$$

- Note that as expected the emitter follower takes the low load resistance and reflects it to the base side, after increasing its value by a factor  $(\beta+1)$ . It is this impedance transformation property of the emitter follower that makes it useful in connecting a low resistance load to a high-resistance source, that is, to implement a buffer amplifier.

*E. Sawires*

## AC analysis

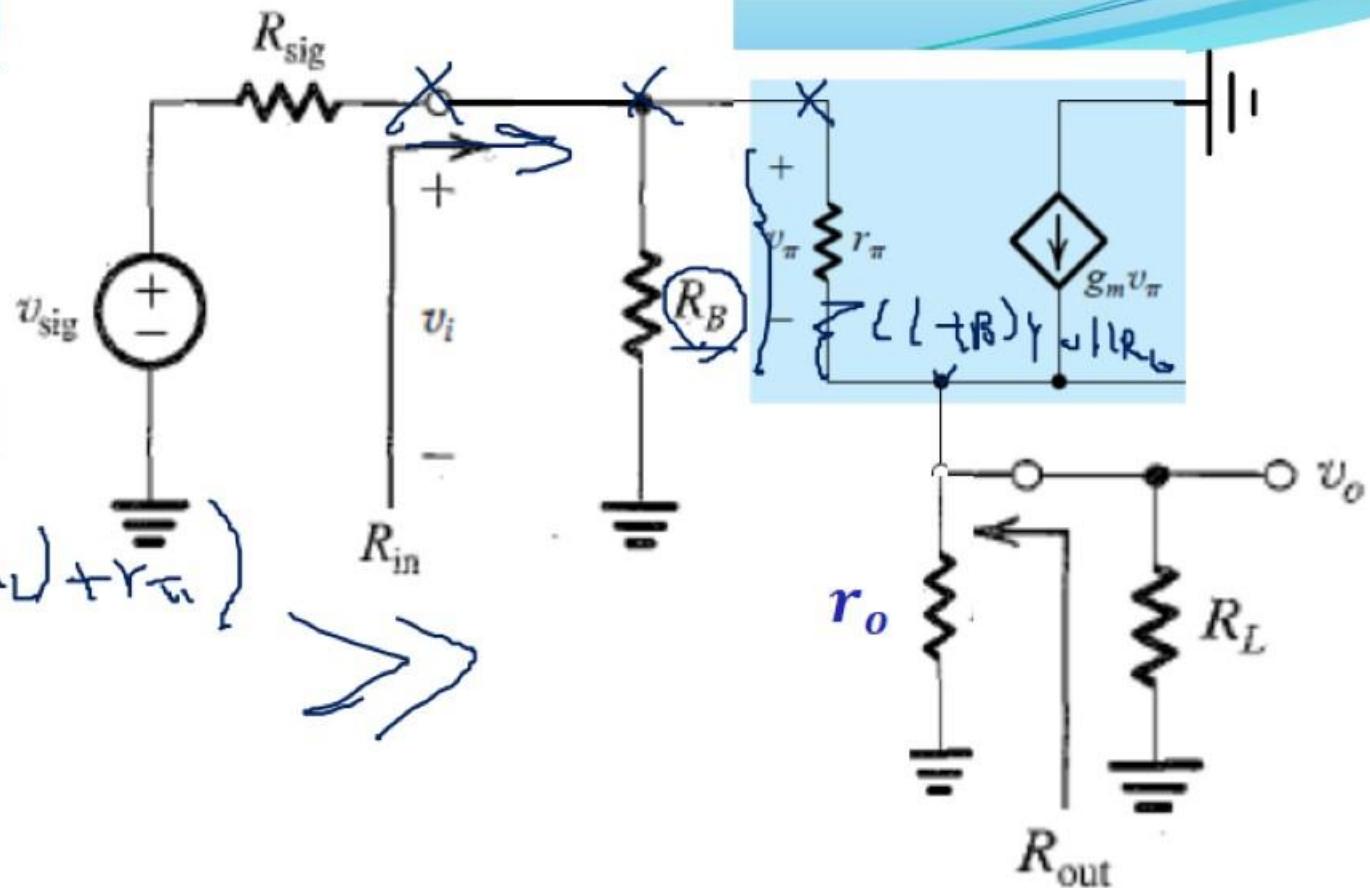


$$k \left( r_o / |R_L| \right)$$

## AC analysis

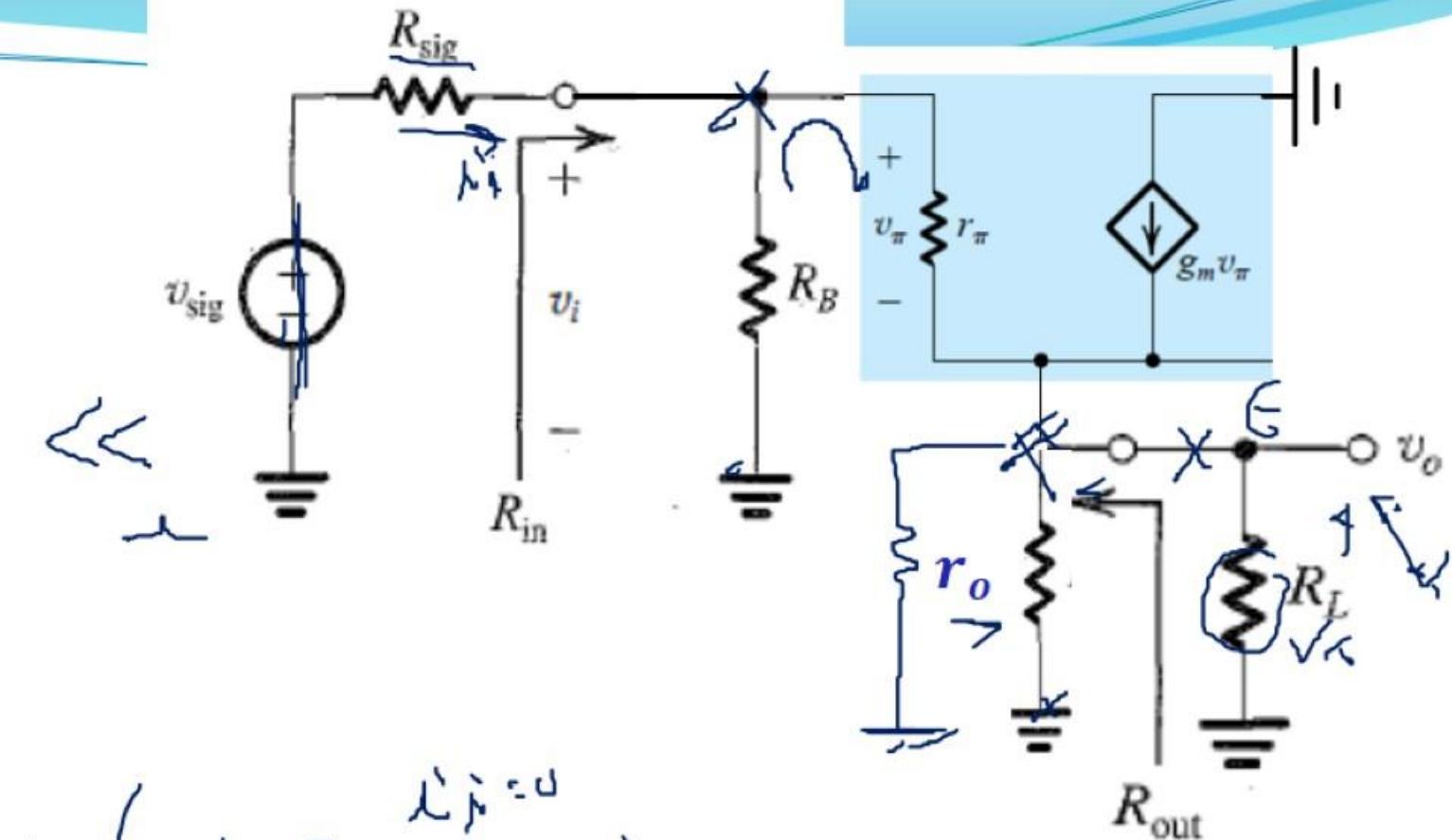
$$R_i = R_B \parallel (\beta + 1)[(r_o \parallel R_L) + r_e]$$

$$R_i = R_B \parallel \left( (\beta + 1)(r_o \parallel R_L) + r_\pi \right)$$



## AC analysis

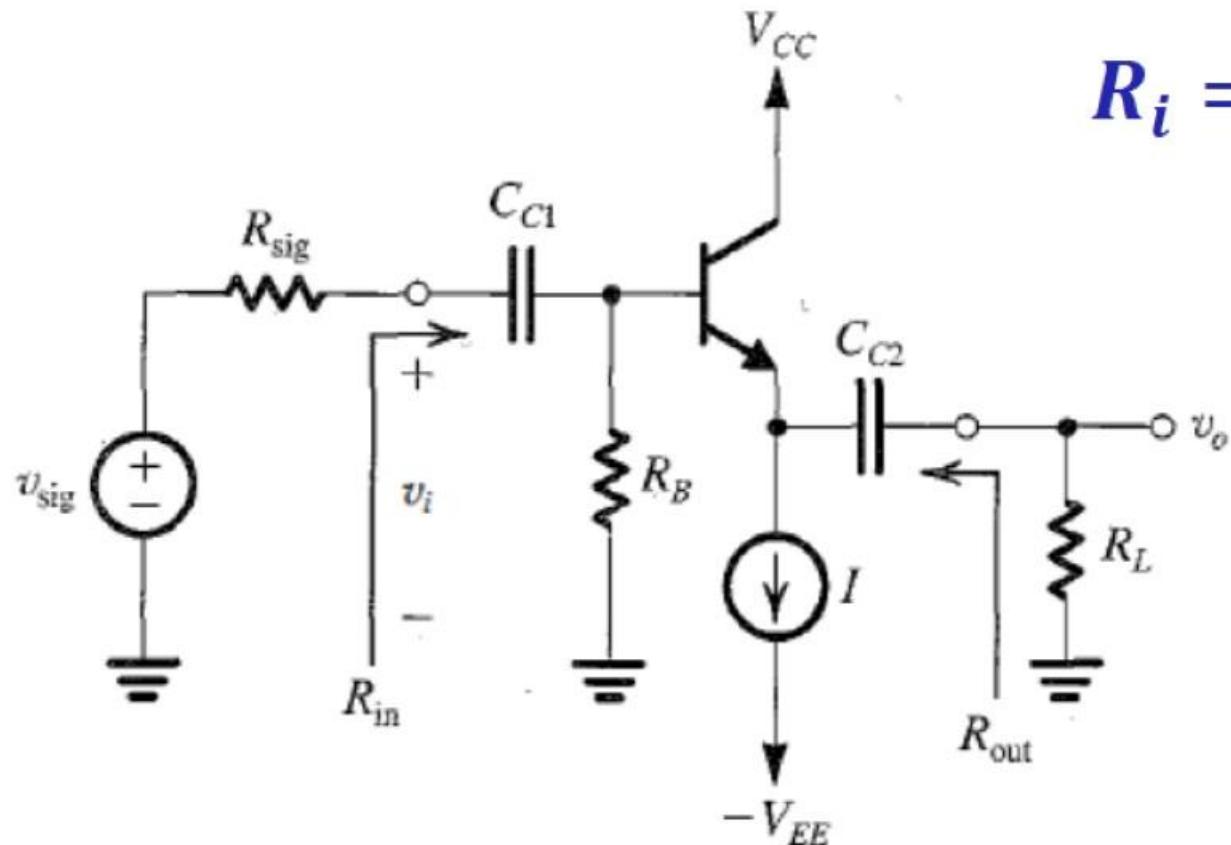
$$R_{\text{out}} = r_o \parallel \left[ r_e + \frac{R_{\text{sig}} \parallel R_B}{\beta + 1} \right]$$



$$r_o \parallel \left( \frac{(R_{\text{sig}} \parallel R_B) + r_\pi}{1 + \beta} \right)$$

# Common Collector or Emitter Follower

Non-Inverting Amplifier



$$R_i = R_B \parallel (\beta + 1)[(r_o \parallel R_L) + r_e] \gg$$

$$A_v = \frac{(r_o \parallel R_L)}{(r_o \parallel R_L) + r_e} \leq 1$$

$$R_{\text{out}} = r_o \parallel \left[ r_e + \frac{R_{\text{sig}} \parallel R_B}{\beta + 1} \right] \ll$$

E. Sawires

# Summary and Comparisons

1. The **CE configuration** is the one best suited for realizing **the bulk of the gain required in an amplifier**. Depending on the magnitude of the gain required, either a single stage or a cascade of two or three stages can be used.
2. Including a resistor in the emitter lead of the CE stage provides a number of performance improvements at the expense of gain reduction.
3. The **low input resistance of the CB amplifier** makes it useful only in specific applications. It has a much **better high-frequency response** than the CE amplifier. This superiority will make it useful as a high-frequency amplifier, especially when combined with the CE circuit.

*E. Sawires*

# Summary and Comparisons

4. The emitter follower (CC) finds application as a voltage buffer for connecting a high resistance source to a low-resistance load and as the output stage in a multistage amplifier, where its purpose is to equip the amplifier with a low output-resistance.

*E. Sawires*

	CE	CB	CC
Voltage gain, $A_v$	High	High	Low $\approx 1$
Current gain, $A_i$	High	Low $\approx 1$	High
Power gain, $A_p$	Very high $\approx A_v A_i$	High $\approx A_v$	High $\approx A_i$
Input resistance, $R_{in(max)}$	moderate to low	Very low	High
Output resistance, $R_{out}$	moderate to high	High	Very low
$\phi$	180	0	0

*Thank You*

???

*Have a Wonderful Semester*